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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Date of Deposit: Jaly 14, 2006

Depositor: Robert Faber

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(Signature & date)

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application of

Date: July 14, 2006

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Huilong Zhu

Group Art Unit: 2826

Serial No: 10/710,244

Examiner: Fazli Erdem

Filed: 06/29/2004

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE:

STRUCTURES AND METHODS FOR MANUFACTURING P-TYPE MOSFET WITH GRADED EMBEDDED SILICON-GERMANIUM SOURCE-DRAIN AND/OR EXTENSION

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

The Commissioner is hereby authorized to charge any and all fees for this submission to Deposit Account No. 09-0458.

Respectfully submitted,

Huilong Zhu

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Jøseph P. Abate Attorney for Applicant

Registration No. 30,238

Telephone No. 845-894-4633

Fax No. 845-892-6363

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